

ABSTRACT:

Semiconductor device.

A semiconductor device comprising a carrier, at least one semiconductor component provided on this carrier, and a multilayer metallization between the semiconductor component and the carrier, wherein a first metal layer of aluminium, gold, or a gold alloy is provided on the surface of the semiconductor component, a second metal layer of titanium is provided on the first metal layer, a third metal layer of nickel is provided on the second metal layer, and a fourth metal layer of a binary or ternary gold-germanium alloy is provided on the third metal layer, is remarkable for its low-ohmic contact and extremely long useful life also under temperature loads.

10 Fig. 1.

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